2N6487, 2N6488 (NPN), 2N6490, 2N6491 (PNP)

Complementary Silicon Plastic Power Transistors

These devices are designed for use in general–purpose amplifier and switching applications.

Features

- High DC Current Gain
- High Current Gain Bandwidth Product
- TO-220 Compact Package
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage 2N6487, 2N6490 2N6488, 2N6491	V _{CEO}	60 80	Vdc
Collector–Base Voltage 2N6487, 2N6490 2N6488, 2N6491	V _{CB}	70 90	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current – Continuous	Ι _C	15	Adc
Base Current	Ι _Β	5.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	75 0.6	W W/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	1.8 0.014	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Indicates JEDEC Registered Data.

THERMAL CHARACTERISTICS

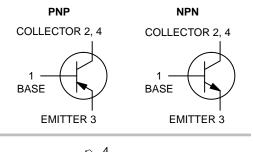
Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	R_{\thetaJC}	1.67	°C/W
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	70	°C/W



ON Semiconductor[®]

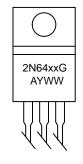
www.onsemi.com

15 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60–80 VOLTS, 75 WATTS





MARKING DIAGRAM



2N64xx = Specific Device Code

- xx = See Table on Page 5 G = Pb-Free Package
- G = Pb–Free Package A = Assembly Location
 - Assembly LocationYear
- Y = Year WW = Work Week

ORDERING INFORMATION See detailed ordering, marking, and shipping information in the package dimensions section on page 5 of this data sheet.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Downloaded from Arrow.com.

2N6487, 2N6488 (NPN), 2N6490, 2N6491 (PNP)

ELECTRICAL CH	HARACTERISTICS (To	c = 25°C unless othe	erwise noted) (Note 2)
---------------	--------------------	----------------------	------------------------

Characteristic	Symbol	Min	Мах	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (Note 3) ($I_C = 200 \text{ mAdc}, I_B = 0$) 2N6487, 2N6490 2N6488, 2N6491	V _{CEO(sus)}	60 80		Vdc
Collector–Emitter Sustaining Voltage (Note 3) (I _C = 200 mAdc, V _{BE} = 1.5 Vdc) 2N6487, 2N6490 2N6488, 2N6491	V _{CEX}	70 90		Vdc
Collector Cutoff Current (V _{CE} = 30 Vdc, I _B = 0) 2N6487, 2N6490 (V _{CE} = 40 Vdc, I _B = 0) 2N6488, 2N6491	ICEO	-	1.0 1.0	mAdc
Collector Cutoff Current ($V_{CE} = 65 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}$) 2N6487, 2N6490 ($V_{CE} = 85 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}$) 2N6488, 2N6491 ($V_{CE} = 60 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_C = 150^{\circ}\text{C}$) 2N6487, 2N6490 ($V_{CE} = 80 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_C = 150^{\circ}\text{C}$) 2N6488, 2N6491	ICEX	- - -	500 500 5.0 5.0	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}, I_C = 0$)	I _{EBO}	_	1.0	mAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 5.0$ Adc, $V_{CE} = 4.0$ Vdc) ($I_C = 15$ Adc, $V_{CE} = 4.0$ Vdc)	h _{FE}	20 5.0	150 -	-
Collector–Emitter Saturation Voltage ($I_C = 5.0 \text{ Adc}, I_B = 0.5 \text{ Adc}$) ($I_C = 15 \text{ Adc}, I_B = 5.0 \text{ Adc}$)	V _{CE(sat)}		1.3 3.5	Vdc
Base-Emitter On Voltage ($I_C = 5.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$) ($I_C = 15 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$)	V _{BE(on)}		1.3 3.5	Vdc
DYNAMIC CHARACTERISTICS				
Current–Gain – Bandwidth Product (Note 4) ($I_C = 1.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}, f_{test} = 1.0 \text{ MHz}$)	f _T	5.0	_	MHz
			1	1

Small–Signal Current Gain
($I_C = 1.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}, f = 1.0 \text{ kHz}$)h----

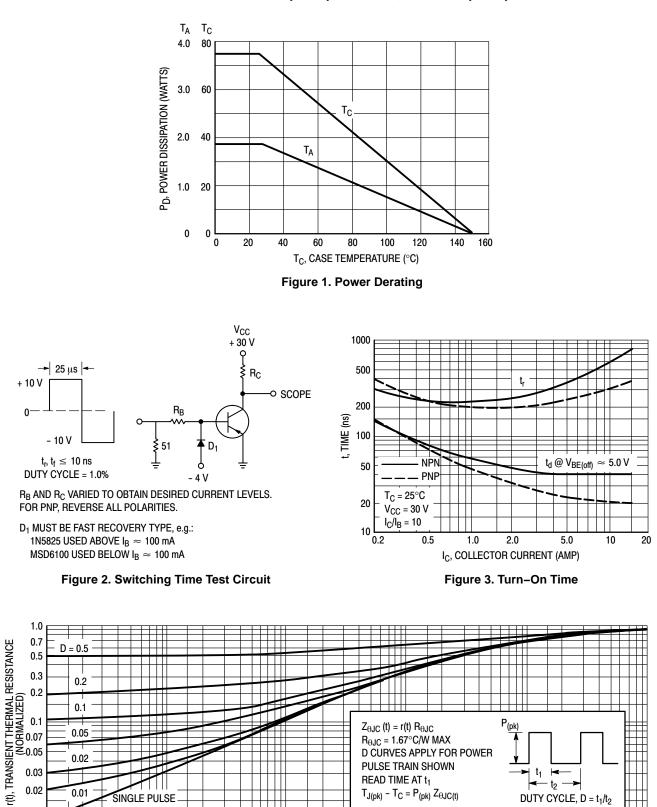
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates JEDEC Registered Data.

3. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

4. $f_T = |h_{fe}| \bullet f_{test}$

2N6487, 2N6488 (NPN), 2N6490, 2N6491 (PNP)





2.0

1.0

 $T_{J(pk)} - T_C = P_{(pk)} Z_{\Theta JC(t)}$

10

20

5.0

t, TIME (ms) **Figure 4. Thermal Response** t₂

100

50

DUTY CYCLE, $D = t_1/t_2$

200

500 1.0 k

0.01

0.02

0.01 🛏 0.01

SINGLE PULSE

0.05

0.1

0.2

0.5

2N6487, 2N6488 (NPN), 2N6490, 2N6491 (PNP)

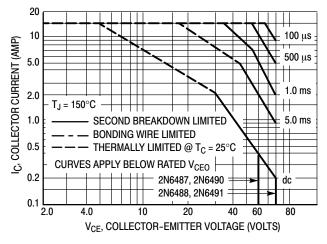


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistors average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

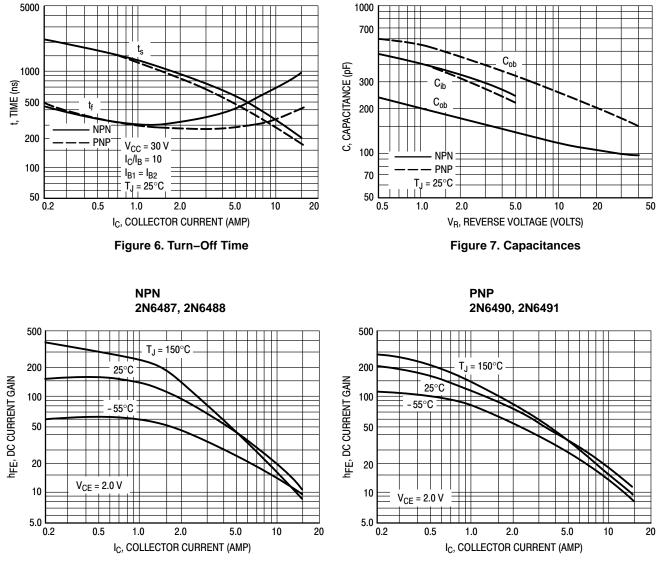


Figure 8. DC Current Gain

2N6487, 2N6488 (NPN), 2N6490, 2N6491 (PNP)

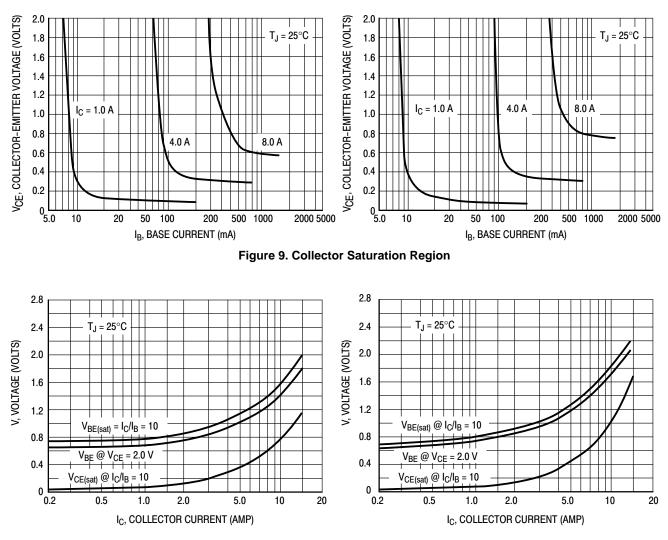


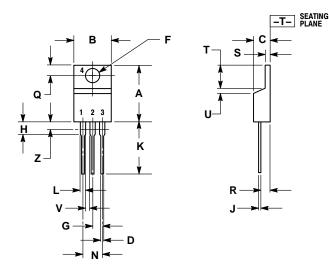
Figure 10. "On" Voltages

ORDERING INFORMATION

Device	Device Marking	Package	Shipping
2N6487G	2N6487	TO-220 (Pb-Free)	50 Units / Rail
2N6488G	2N6488	TO-220 (Pb-Free)	50 Units / Rail
2N6490G	2N6490	TO-220 (Pb-Free)	50 Units / Rail
2N6491G	2N6491	TO-220 (Pb-Free)	50 Units / Rail

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED

	INCHES		MILLIN	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
κ	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
Ν	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
۷	0.045		1.15	
Ζ		0.080		2.04

STYLE 1: BASE PIN 1. 2. COLLECTOR FMITTER 3 COLLECTOR

ON Semiconductor and the 💷 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other industries, Ltc (SoLLC product) of its substants in the United States and/or other Countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other industries, Ltc (SoLLC) of its substants in the United States and/or other Countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other industries, Ltc (SoLLC) of its substants in the United States and/or other Countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other industries, Ltc (SoLLC) of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights or other, sustain life, or for any data and other survival or authorized for use a component is number to survival into the body or other applications. or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative